

WHAT IS CLAIMED IS:

1. A solid-state imaging device having a gate structure including an oxide film and a nitride film, comprising:

upper layer films allowing ultraviolet rays having a frequency of 400 nm or less to pass therethrough; and a metal made shield film formed in such a manner as to cover a region of said gate structure including an oxide film and a nitride film, excluding a light receiving portion and a transfer portion, of said solid-state imaging device.

2. A solid-state imaging device according to claim 1, wherein said metal made shield film has an opening at a position directly over a floating diffusion region of said solid-state imaging device.

3. A solid-state imaging device having a gate structure including an oxide film and a nitride film, comprising:

upper layer films allowing ultraviolet rays having a frequency of 400 nm or less to pass therethrough; and an organic film capable of absorbing said ultraviolet rays, said organic film being formed in such a manner as to cover a region of said gate structure including an oxide film and a nitride film, excluding a

light receiving portion and a transfer portion, of said solid-state imaging device.